

isc N-Channel MOSFET Transistor

IPS60R3K4CE

• FEATURES

- With TO-251(IPAK) packaging
- · High speed switching
- Easy to use
- 100% avalanche tested
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation



- Power supply
- DC-DC converters
- Motor control
- Switching applications



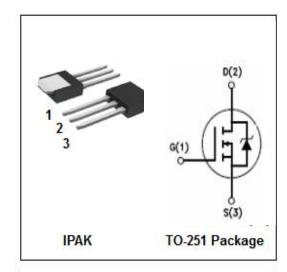


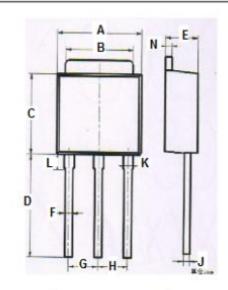
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|--------------------------------|---------|----------------------|
| V_{DSS} | Drain-Source Voltage | 600 | V |
| V _{GSS} | Gate-Source Voltage | ±30 | V |
| I _D | Drain Current-Continuous | 2.6 | А |
| I _{DM} | Drain Current-Single Pulsed | 3.9 | А |
| P _D | Total Dissipation | 29 | W |
| T _j | Operating Junction Temperature | -40~150 | $^{\circ}\mathbb{C}$ |
| T _{stg} | Storage Temperature | -40~150 | ${}^{\mathbb{C}}$ |

• THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | | UNIT | |
|-----------|---------------------------------------|------|------|--|
| Rth(ch-c) | Channel-to-case thermal resistance | 4.26 | °C/W | |
| Rth(ch-a) | Channel-to-ambient thermal resistance | 62 | °C/W | |





| | mm | | |
|-----|------|------|--|
| DIM | MIN | MAX | |
| Α | 6.40 | 6.48 | |
| В | 5.10 | 5.50 | |
| C | 5.80 | 6.20 | |
| D | 9.20 | 9.60 | |
| E | 2.20 | 2.40 | |
| F | 0.50 | 0.70 | |
| G | 2.09 | 2.49 | |
| Н | 2.09 | 2.49 | |
| J | 0.40 | 0.60 | |
| K | 0.70 | 0.90 | |
| L | 1.60 | 2.00 | |
| N | 0.40 | 0.60 | |

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|---------------------|--------------------------------|---|-----|------|----------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D = 0.25mA | 600 | | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} ; I _D =0.04mA | 2.5 | | 3.5 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =0.5A | | 3.17 | 3.4 | Ω |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} = ±20V;V _{DS} = 0V | | | ±0.1 | μА |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} = 600V; V _{GS} = 0V;Tj=25℃ V _{DS} = 600V; V _{GS} = 0V;Tj=150℃ | | | 1 100 | μА |
| V _{SDF} | Diode forward voltage | I _{SD} =0.6A, V _{GS} =0V | | 0.9 | | V |

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